

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Fast switching.
2. High reliability.
3. High current capability.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Rectifier for high voltage power supply.
2. General purpose high voltage rectifier. .
3. Rectification for X-ray generator high voltage power supply.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.65 grams (approx).

SHAPE DISPLAY:

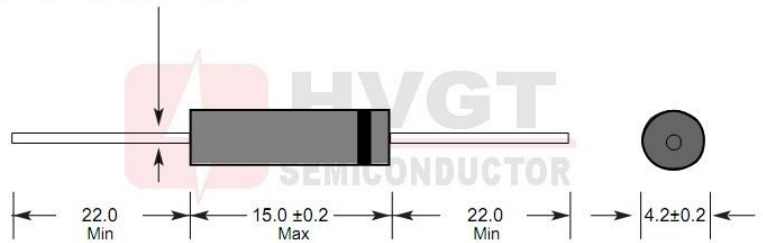


SIZE: (Unit:mm)

HVGT NAME: DO-415

DO-415 Series

Lead Diameter 0.8mm ±0.03



Unit:mm

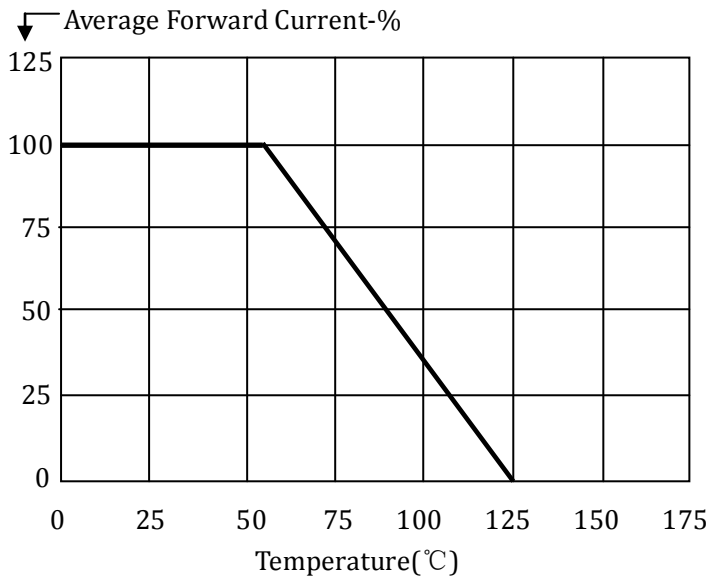
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

| Items | Symbols | Condition | Data Value | Units |
|--------------------------------------|------------|--|------------|-------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | $T_A=25^{\circ}C$ | 12 | kV |
| Non-Repetitive Peak Reverse Voltage | V_{RSM} | $T_A=25^{\circ}C$ | -- | kV |
| Average Forward Current Maximum | I_{FAVM} | $T_A=40^{\circ}C$ | 170 | mA |
| | | $T_{OIL}=55^{\circ}C$ | 300 | mA |
| Non-Repetitive Forward Surge Current | I_{FSM} | $T_A=25^{\circ}C$; 60Hz Half-Sine Wave; 8.3ms | 15 | A |
| Junction Temperature | T_J | | 125 | $^{\circ}C$ |
| Allowable Operation Case Temperature | T_C | | -40~+125 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | | -40~+150 | $^{\circ}C$ |

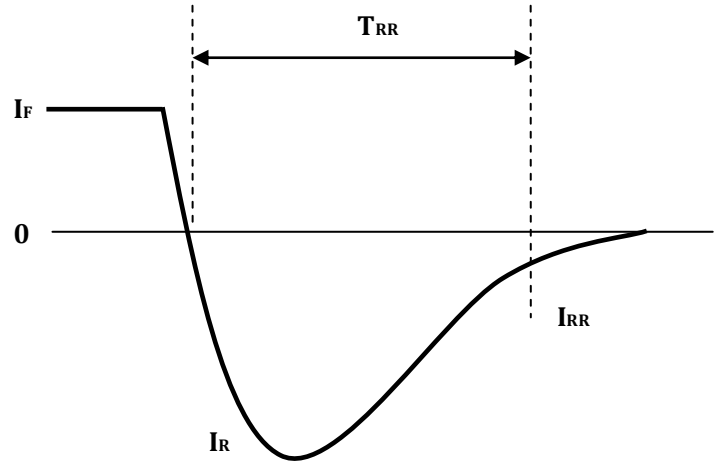
ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

| Items | Symbols | Condition | Data value | Units |
|-------------------------------|----------|---|------------|---------|
| Maximum Forward Voltage Drop | V_{FM} | at $25^{\circ}C$; at 100mA | 30 | V |
| Maximum Reverse Current | I_{R1} | at $25^{\circ}C$; at V_{RRM} | 2.0 | μA |
| | I_{R2} | at $100^{\circ}C$; at V_{RRM} | 10 | μA |
| Maximum Reverse Recovery Time | T_{RR} | at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$ | 80 | nS |
| Junction Capacitance | C_J | at $25^{\circ}C$; $V_R=0V$; $f=1MHz$ | 4.6 | pF |

Forward Current Derating Curve

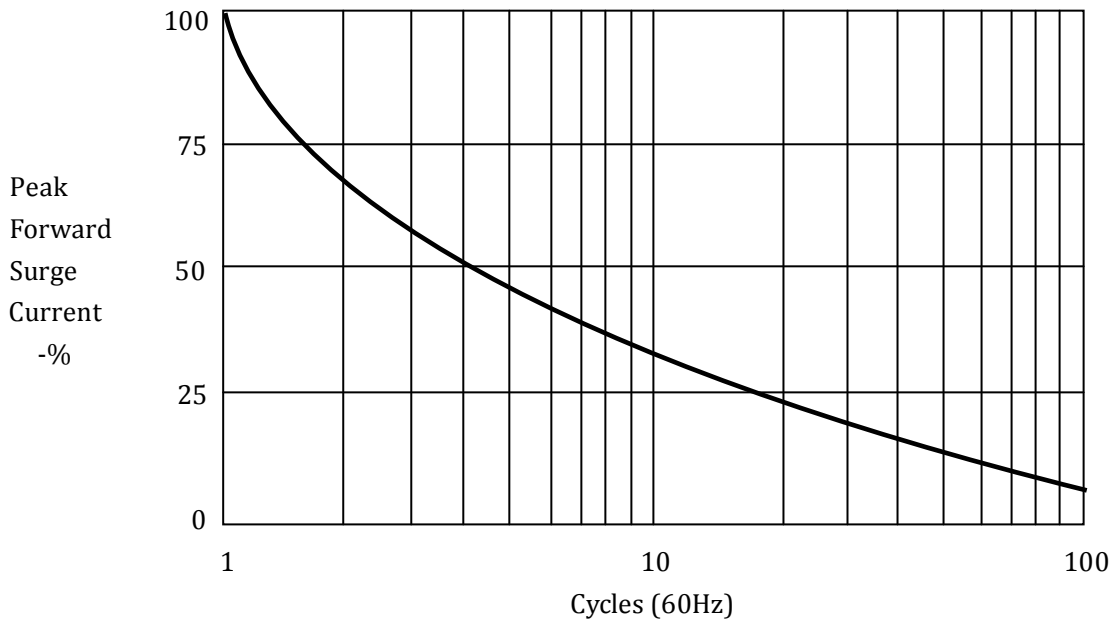


Reverse Recovery Measurement Waveform



Typical data capture points: $I_F = 0.5I_R$, $I_R, I_{RR} = 0.25I_R$
 I_R is typically the rated average forward current maximum (I_{FAVM}) of the D.U.T

Non-Repetitive Surge Current



| Marking | Type | Code | Cathode Mark |
|---------|------------|--------------------|--------------|
| | ESJC37-12F | ESJC37-12F HVGT | |